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APR 16 2002  
PATENT & TRADEMARK OFFICE

# AMENDMENT TRANSMITTAL LETTER

Docket No.  
M4065.0166/P166-A  
Art Unit  
1765

Application No.  
09/643,946

Filing Date  
August 23, 2000

Examiner  
L. Vinh

Applicant(s): Kevin J. Torek et al.

Invention: ACID BLEND FOR REMOVING ETCH RESIDUE

## TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an Amendment Under 37 CFR 1.116 in the above-identified application.  
The fee has been calculated as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	19	- 22 =	0	x	
Independent Claims	3	- 3 =	0	x	
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0

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- ☒ Large Entity ☐ Small Entity
- ☒ No additional fee is required for this Amendment.
- ☐ Please charge Deposit Account No. \_\_\_\_\_ in the amount of \$ \_\_\_\_\_.  
A duplicate copy of this sheet is enclosed.
- ☐ A check in the amount of \$ \_\_\_\_\_ to cover the filing fee is enclosed.
- ☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 04-1073 as described below.
- ☒ Credit any overpayment.
- ☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.

*MA D'Amico*  
~~Thomas J. D'Amico~~ **MARK THROMON**  
Attorney Reg. No.: ~~28,371~~ **33,082**

Dated: April 16, 2002

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Docket No.: M4065.0166/P166-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Kevin J. Torek et al.

Application No.: 09/643,946

Group Art Unit: 1765

Filed: August 23, 2000

Examiner: L. Vinh

For: ACID BLEND FOR REMOVING ETCH  
RESIDUE

AMENDMENT UNDER 37 C.F.R. § 1.116

ATTN: Box AF  
Commissioner for Patents  
Washington, DC 20231

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Dear Sir:

In response to the final Office Action dated January 16, 2002 (Paper No. 7),  
please amend the above-captioned application as follows:

**In the Claims:**

Replace claims 142, 150 and 158 with amended claims 142, 150 and 158 below.

500 →  
V,  
142. (Twice Amended) A conditioning solution for use in removing residues  
remaining on a semiconductor substrate after a dry etch process, said conditioning solution  
comprising:

hydrofluoric acid;

phosphoric acid;

propylene glycol and